

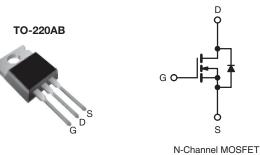
Vishay Siliconix

RoHS

COMPLIANT

Power MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
R _{DS(on)} (Ω)	$V_{GS} = 5.0 V$	0.028			
Q _g (Max.) (nC)	66				
Q _{gs} (nC)	12				
Q _{gd} (nC)	43				
Configuration	Single				



FEATURES

- Dynamic dV/dt Rating
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS} = 4 V$ and 5 V
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRLZ44PbF
	SiHLZ44-E3
SnPb	IRLZ44
	SiHLZ44

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \text{ °C}$, unless otherwise noted)							
PARAMETER			SYMBOL	LIMIT	UNIT		
Drain-Source Voltage			V _{DS}	60	v		
Gate-Source Voltage			V _{GS}	± 10			
Continuous Drain Current ^e	V _{GS} at 5.0 V -	T _C = 25 °C	- I _D	50	А		
Continuous Drain Current		T _C = 100 °C		36			
Pulsed Drain Current ^a			I _{DM}	200			
Linear Derating Factor				1.0	W/°C		
Single Pulse Avalanche Energy ^b			E _{AS}	400	mJ		
Maximum Power Dissipation	T _C = 25 °C		P _D	150	W		
Peak Diode Recovery dV/dt ^c			dV/dt	4.5	V/ns		
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 175			
Soldering Recommendations (Peak Temperature) ^d	for 10 s			300	- °C		
Mounting Torque	6-32 or M3 screw			10	lbf ∙ in		
				1.1	N · m		

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. $V_{DD} = 25 \text{ V}$, starting $T_J = 25 \text{ °C}$, L = 179 µH, $R_g = 25 \Omega$, $I_{AS} = 51 \text{ A}$ (see fig. 12). c. $I_{SD} \le 51 \text{ A}$, $dV/dt \le 250 \text{ A/s}$, $V_{DD} \le V_{DS}$, $T_J \le 175 \text{ °C}$.

- d. 1.6 mm from case.
- e. Current limited by the package, (die current = 51 A).

* Pb containing terminations are not RoHS compliant, exemptions may apply

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